EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	19	(capacitor same trench) and aberrat$3 and pattern	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 08:04
L2	21	(capacitor same trench) and aberrat$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 08:07
L3	1370	capacitor and aberrat$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 08:08
L4	61	capacitor same aberrat$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 08:08
L5	7	capacitor same aberrat$3 and trench	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 10:29
L6	305	(capacitor with trench) same (test$3 or examin$3 or evaluat$3 or estimat$3 or check$3 or verif$3 or monitor$3 or assessment or analyz$3 or analysis)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 08:40
L7	3	(capacitor with trench) same (test$3 or examin$3 or evaluat$3 or estimat$3 or check$3 or verif$3 or monitor$3 or assessment or analyz$3 or analysis) and aberrat$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 09:40
L8	2	(capacitor with trench) same (test$3 or examin$3 or evaluat$3 or estimat$3 or check$3 or verif$3 or monitor$3 or assessment or analyz$3 or analysis) and aberrat$3 and (pattern same layout)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 09:41
L9	3	(capacit$4 with trench) same (test$3 or examin$3 or evaluat$3 or estimat$3 or check$3 or verif$3 or monitor$3 or assessment or analyz$3 or analysis) and aberrat$3 and (pattern same layout)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 09:41

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L10	3	(capacit$4 same trench) same (test$3 or examin$3 or evaluat$3 or estimat$3 or check$3 or verif$3 or monitor$3 or assessment or analyz$3 or analysis) and aberrat$3 and (pattern same layout)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 10:26
L11	13	(trench or DT) same (test$3 or examin$3 or evaluat$3 or estimat$3 or check$3 or verif$3 or monitor$3 or assessment or analyz$3 or analysis) and aberrat$3 and (pattern same layout)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 09:46
L12	9	(trench or DT) same (test$3 or examin$3 or evaluat$3 or estimat$3 or check$3 or verif$3 or monitor$3 or assessment or analyz$3 or analysis) and aberrat$3 and (pattern same layout same (shape or H))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 09:47
L13	9	(trench or DT) same (test$3 or examin$3 or evaluat$3 or estimat$3 or check$3 or verif$3 or monitor$3 or assessment or analyz$3 or analysis) and aberrat$3 and (pattern same layout same (shape or "H"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 09:54
L14	5	(capacitor with (deep adj trench) or DT or trench) same layout same "H" and aberrat$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 10:22
L15	5	(capacitor with (deep adj trench) or DT or trench) same layout same "H" and (aberrat$4 or unsymmetr$4 or assymetr$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 10:23
L16	5	(capacitor with (deep adj trench) or DT or trench) same layout same "H" and (aberrat$4 or unsymmetr$4 or asymetr$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 10:25
L17	3	(capacit$4 same trench) same (test$3 or examin$3 or evaluat$3 or estimat$3 or check$3 or verif$3 or monitor$3 or assessment or analyz$3 or analysis) and (aberrat$4 or unsymmetr$4 or asymetr$4) and (pattern same layout)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 10:26
L18	15	capacitor same (aberrat$4 or unsymmetr$4 or asymetr$4) and trench	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 10:29

L21	6	(capacitor same trench) and (aberrat$4 or unsymmetr$4 or asymetr$4) and (pattern same test)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 13:46
L22	19	(capacitor same trench) and (pattern same test same (length or width or distance))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 13:48
L23	9	(capacitor same trench) and (pattern same test same (length or width or distance)) and (photomask or photolithography)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 13:48
L24	14	(capacitor same trench) and (pattern same test same (length or width or distance)) and (photomask or photolithography or lithography)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 15:10
L25	152	((capacitor same trench) same (layout or pattern) same (distance or length or width)) and (photomask or photolithography or lithography)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 15:11
L26	83	((capacitor same trench) same (layout or pattern) same (distance or length or width)) same (photomask or photolithography or lithography or mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 15:11
L27	69	((capacitor with trench) same (layout or pattern) same (distance or length or width)) same (photomask or photolithography or lithography or mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 15:21
L28	3	((capacitor with trench) same (layout or pattern) same (distance or length or width) same pair) same (photomask or photolithography or lithography or mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 15:33
L29	13	((capacitor with trench) same (layout or pattern) same (distance or length or width) same pair) and (photomask or photolithography or lithography or mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 15:33
S1	23	(lens near3 aberration near3 effect) and "716"/$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 15:21

S2	5	(lens near3 aberration near3 effect) and (test with pattern) and "716"/$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 15:27
S3	2	"20050229147"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 15:25
S4	1	(lens near3 aberration near3 effect) and (test same pattern) and ((deep adj2 trench) same capacit$4) and "716"/$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 15:29
S5	1	(lens near3 aberration near3 effect) and test and ((deep adj2 trench) same capacit$4) and "716"/$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 15:29
S6	1	(lens near3 aberration near3 effect) and (test$3 or verif$3 or check$3 or monitor$3 or analysis or analyz$3 or estimat$3 or evaluat$3 or assessment or examin$3) and (((deep adj2 trench) or DT) same capacit$4) and "716"/$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 15:44
S7	1	(fabricat$3 same (capacitor with (DT or (deep adj2 trench)))) and aberrat$3 and COMA and ((S3 or three) adj foil)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 15:46
S8	1	(fabricat$3 same capacitor same trench) and aberrat$3 and COMA and ((S3 or three) adj foil)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 15:46
S9	1	(fabricat$3 same capacitor same trench) and aberrat$3 and ((S3 or three) adj foil)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 15:47
S10	8	(fabricat$3 same capacitor same trench) and aberrat$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 16:01

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S11	15	((fabricat$3 or manufactur$3) same capacitor same trench) and aberrat$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 16:18
S12	13	((fabricat$3 or manufactur$3) same capacitor same trench) and aberrat$3 and pattern	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 16:02
S13	1	"6163376".PN.	USPAT; USOCR	OR	ON	2006/06/05 16:16
S14	2	((fabricat$3 or manufactur$3) same capacitor same trench) and aberrat$3 and (test near3 area)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 16:19
S15	2	((fabricat$3 or manufactur$3) same capacitor same trench) and aberrat$3 and ((test near3 area) with layout)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 16:20
S16	13	((fabricat$3 or manufactur$3) same capacitor same trench) and aberrat$3 and pattern	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 10:34

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IEEE CNF	IEEE Conference Proceeding
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